Abstracts

Recent Advancements in Gallium Arsenide Devices (Panel)

G.L. McCoy. "Recent Advancements in Gallium Arsenide Devices (Panel)." 1974 S-MTT International Microwave Symposium Digest of Technical Papers 74.1 (1974 [MWSYM]): 150-150.

This panel will discuss recent work done on three devices which are presently in the forefront of microwave technology. These devices are the GaAs IMPATT diodes for X and Ka-band, Gunn diodes for X and Ka-band, and Field Effect Transistors for C and X-band. Discussion by the panel will include a short presentation by each panel member highlighting recent advancements in his area. Presentations will include discussion of the basic devices and applications of devices. The panel will conclude with a summary of projected performance for the IMPATT, Gunn and FET devices.

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